Unit in mm

TOSHIBA Diode Silicon Epitaxial Planar Type

# **1SS193**

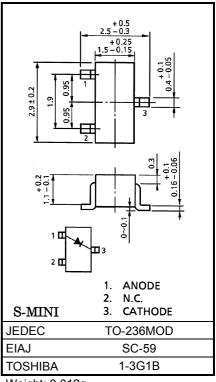
## **Ultra High Speed Switching Application**

■ Small package : SC-59

 $\begin{array}{ll} \bullet & \text{Low forward voltage} & : V_{F~(3)} = 0.9 V \text{ (typ.)} \\ \bullet & \text{Fast reverse recovery time: } t_{rr} = 1.6 \text{ns (typ.)} \\ \bullet & \text{Small total capacitance} & : C_{T} = 0.9 \text{pF (typ.)} \\ \end{array}$ 

## **Maximum Ratings (Ta = 25°C)**

Characteristic	Symbol	Rating	Unit
Maximum (peak) reverse voltage	$V_{RM}$	85	V
Reverse voltage	V <sub>R</sub>	80	V
Maximum (peak) forward current	I <sub>FM</sub>	300	mA
Average forward current	Io	100	mA
Surge current (10ms)	I <sub>FSM</sub>	2	А
Power dissipation	Р	150	mW
Junction temperature	Tj	125	°C
Storage temperature range	T <sub>stg</sub>	-55~125	°C

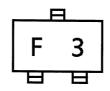


Weight: 0.012g

### **Electrical Characteristics (Ta = 25°C)**

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Forward voltage	V <sub>F (1)</sub>	_	I <sub>F</sub> =1mA	_	0.60	_		
	V <sub>F (2)</sub>	_	I <sub>F</sub> = 10mA	_	0.72	_	V	
	V <sub>F (3)</sub>	_	I <sub>F</sub> = 100mA	_	0.90	1.20		
Reverse current	I <sub>R (1)</sub>	_	V <sub>R</sub> = 30V	_	_	0.1	^	
	I <sub>R (2)</sub>	_	V <sub>R</sub> = 80V	_	_	0.5	μΑ	
Total capacitance	C <sub>T</sub>	_	V <sub>R</sub> = 0, f = 1MH <sub>z</sub>	_	0.9	3.0	pF	
Reverse recovery time	t <sub>rr</sub>	_	I <sub>F</sub> = 10mA (Fig.1)	_	1.6	4.0	ns	

#### Marking



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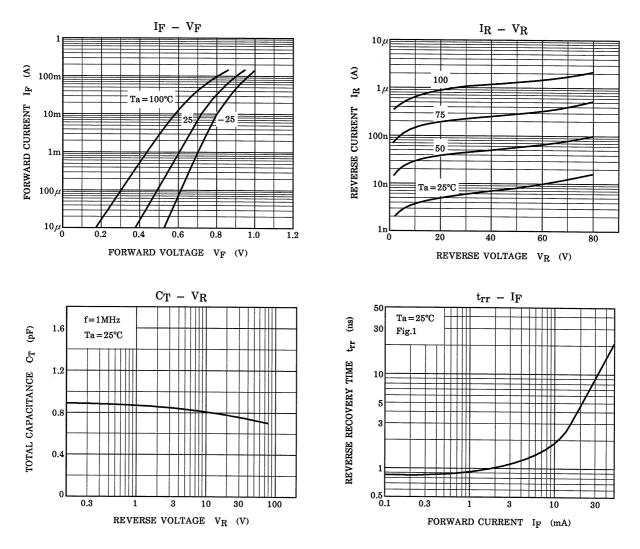
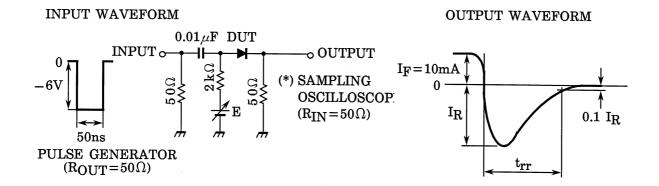


Fig.1 Reverse recovery time (trr) test circuit



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